

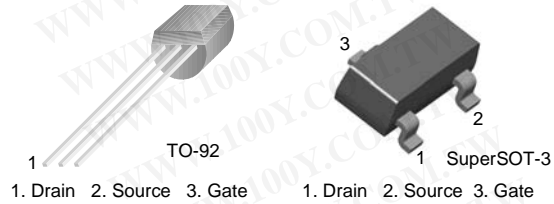
勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-54151736
 勝特力电子(深圳) 86-755-83298787
 Http://www.100y.com.tw

FAIRCHILD
 SEMICONDUCTOR®

J108/J109/J110/MMBFJ108

N-Channel Switch

- This device is designed for digital switching applications where very low on resistance is mandatory.
- Sourced from Process 58.



Absolute Maximum Ratings * $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	25	V
V_{GS}	Gate-Source Voltage	-25	V
I_{GF}	Forward Gate Current	10	mA
T_J, T_{stg}	Operating and Storage Junction Temperature Range	-55 ~ +150	$^\circ\text{C}$

* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

- These ratings are based on a maximum junction temperature of 150 degrees C.
- These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Electrical Characteristics $T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristics						
$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	$I_G = -10\mu\text{A}, V_{DS} = 0$	-25			V
I_{GSS}	Gate Reverse Current	$V_{GS} = -15\text{V}, V_{DS} = 0$			-3.0	nA
		$V_{GS} = -15\text{V}, V_{DS} = 0, T_A = 100^\circ\text{C}$			-200	nA
$V_{GS(off)}$	Gate-Source Cutoff Voltage	$V_{DS} = 15\text{V}, I_D = 10\text{nA}$	108	-3.0	-10	V
			109	-2.0	-6.0	V
			110	-0.5	-4.0	V
On Characteristics						
I_{DSS}	Zero-Gate Voltage Drain Current *	$V_{DS} = 15\text{V}, I_{GS} = 0$	108	80		mA
			109	40		mA
			110	10		mA
$r_{DS(on)}$	Drain-Source On Resistance	$V_{DS} \leq 0.1\text{V}, V_{GS} = 0$	108		8.0	Ω
			109		12	Ω
			110		18	Ω
Small Signal Characteristics						
$C_{dg(on)}$	Drain Gate & Source Gate On Capacitance	$V_{DS} = 0, V_{GS} = 0, f = 1.0\text{MHz}$			85	pF
$C_{sg(off)}$	Source-Gate Off Capacitance				15	pF
$C_{dg(off)}$	Drain-Gate Off Capacitance	$V_{DS} = 0, V_{GS} = -10, f = 1.0\text{MHz}$			15	pF
$C_{sg(off)}$	Source-Gate Off Capacitance	$V_{DS} = 0, V_{GS} = -10, f = 1.0\text{MHz}$			15	pF

* Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$

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Thermal Characteristics $T_A=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Max.		Units
		J108 - 110	*MMBFJ108	
P _D	Total Device Dissipation Derate above 25°C	625	350	mW
		5.0	2.8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	125		°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	357	556	°C/W

* Device mounted on FR-4 PCB 1.6" × 1.6" × 0.06"

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Typical Characteristics

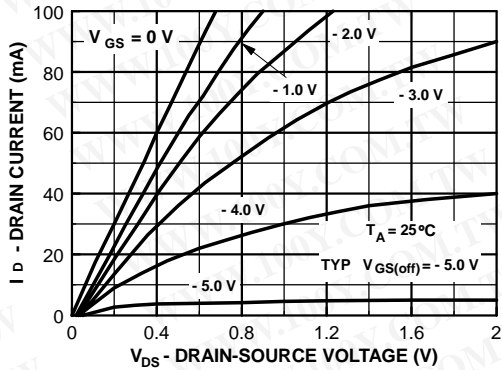


Figure 1. Common Drain-Source

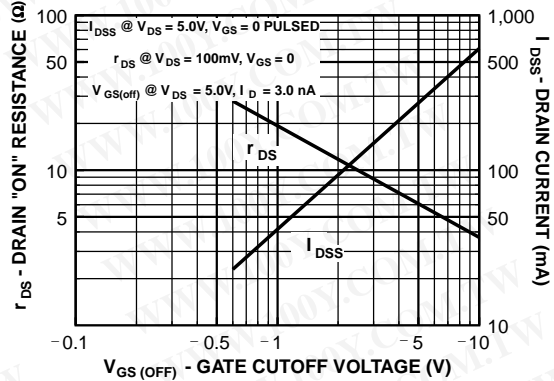


Figure 2. Parameter Interactions

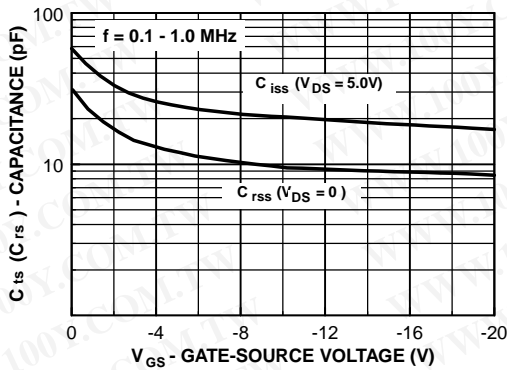


Figure 3. Common Drain-Source

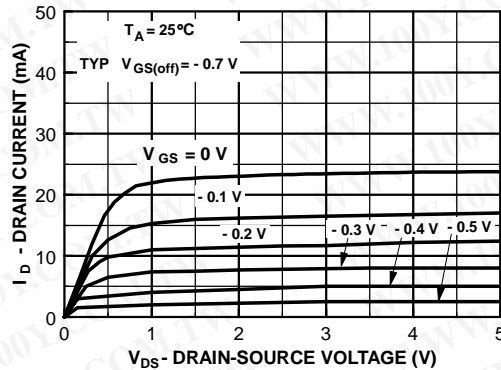


Figure 4. Common Drain-Source

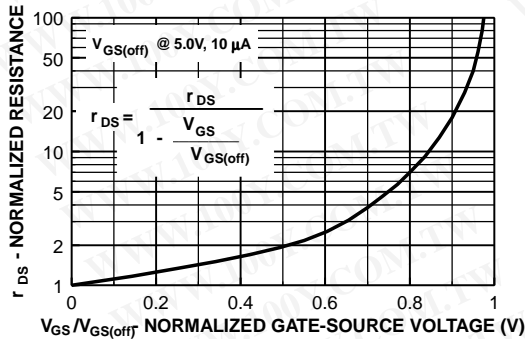


Figure 5. Normalized Drain Resistance vs Bias Voltage

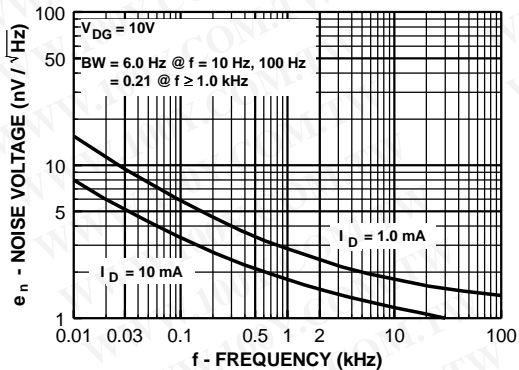


Figure 6. Noise Voltage vs Frequency

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Typical Characteristics (Continued)

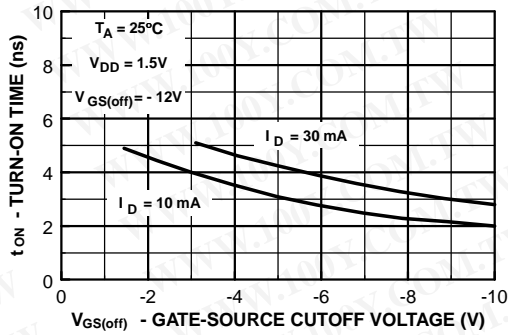


Figure 7. Switching Turn-On Time vs Gate-Source Cutoff Voltage

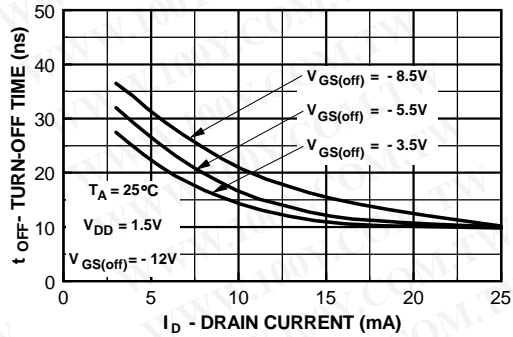


Figure 8. Switching Turn-Off Time vs Drain Current

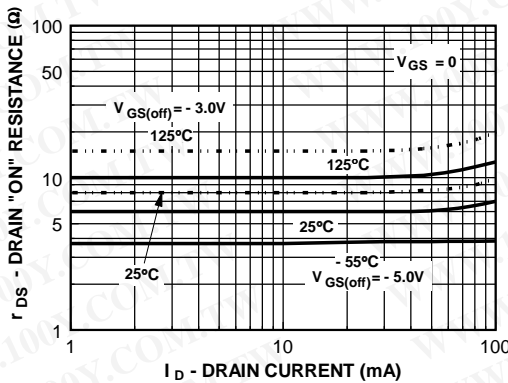


Figure 9. On Resistance vs Drain Current

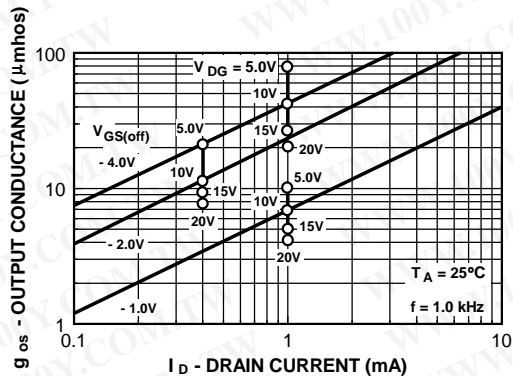


Figure 10. Output Conductance vs Drain Current

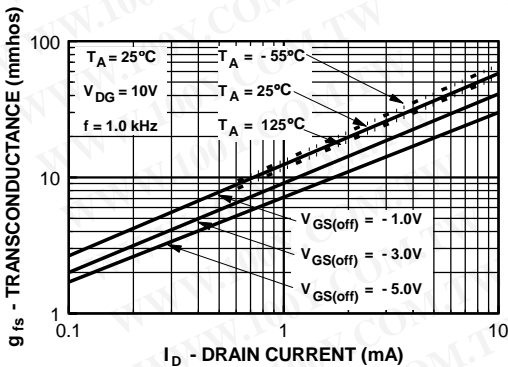


Figure 11. Transconductance vs Drain Current

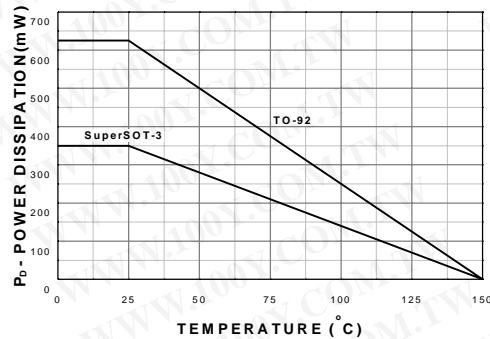
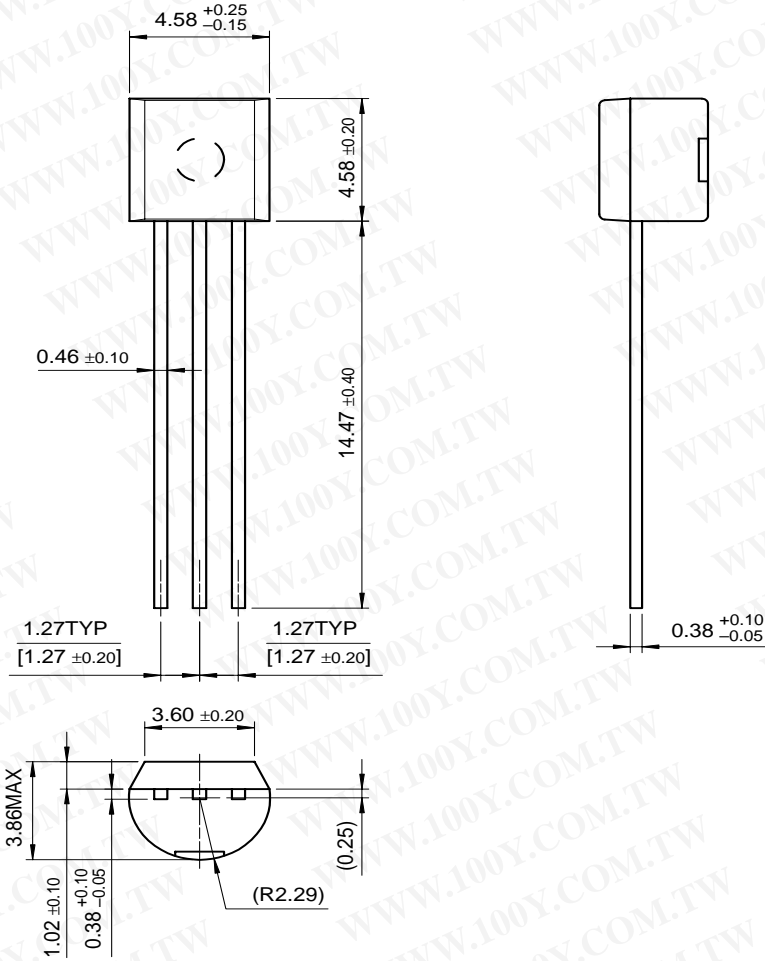


Figure 12. Power Dissipation vs Ambient Temperature

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Package Dimensions

TO-92



J108/J109/J110/MMBF-J108

Dimensions in Millimeters

